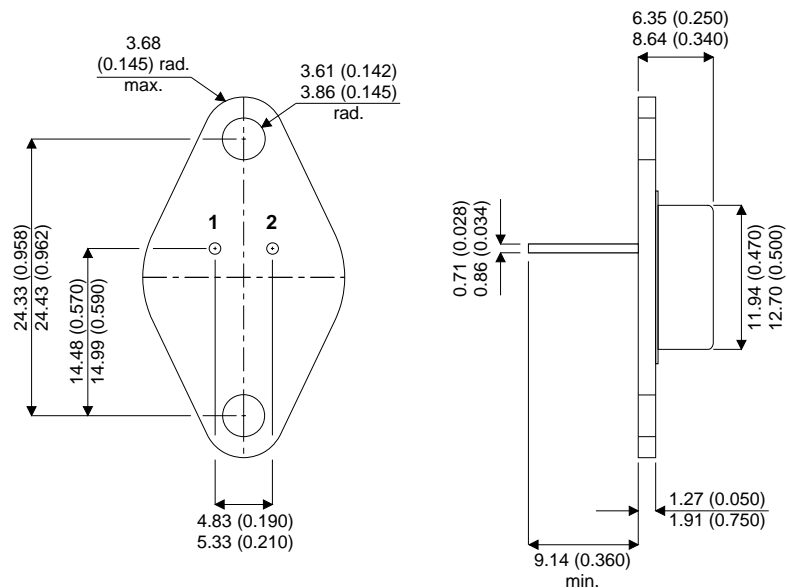


**MECHANICAL DATA**

Dimensions in mm (inches)

**NPN DRIVER TRANSISTOR**



**TO-66 Metal Package.**

Pin 1 – Base      Pin 2 – Emitter      Case – Collector

- Bipolar Power Transistor
- TO-66 Hermetic Package
- Fast Switching

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$V_{CEO}$	Collector – Emitter Voltage	60V
$I_C$	Continuous Collector Current	3A
$P_D$	Total Device Dissipation	16W
	Derate above 100°C	6.25°C/W
$T_{STG}, T_J$	Storage and Operating Junction Temperature Range	-55 to +200°C

Parameter		Test Conditions		Min.	Typ.	Max.	Units
$BV_{CEO}$	Collector – Emitter Breakdown Voltage	$I_C = 50\text{mA}$		60			V
$BV_{EBO}$	Emitter – Base Breakdown Voltage	$I_E = 100\mu\text{A}$		7			
$BV_{CBO}$	Collector – Base Breakdown Voltage	$I_C = 100\mu\text{A}$		60			
$I_{CEO}$	Collector Cut-off Current	$V_{CE} = 60\text{V}$				20	$\mu\text{A}$
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = 6\text{V}$				5	
$I_{CES}$	Emitter Cut-off Current	$V_{CE} = 60\text{V}$				20	
$H_{FE1}$	Current Gain	$V_{CE} = 10\text{V}$	$I_C = 0.5\text{A}$	40		120	—
$H_{FE2}$	Current Gain	$V_{CE} = 10\text{V}$	$I_C = 0.2\text{A}$	30		120	
$h_{fe}$	Current Gain	$V_{CE} = 15\text{V}$ $f = 10\text{MHz}$	$I_C = 0.5\text{A}$	3			—
$C_{ob}$	Output Capacitance	$V_{CB} = 10\text{V}$	$f = 1\text{MHz}$			160	pF
$V_{CEO(sus)}$	Collector – Emitter Saturation Voltage	$I_C = 2\text{A}$	$I_B = 0.2\text{A}$			0.8	V
$V_{BEO(sus)}$	Base – Emitter Saturation Voltage	$I_C = 2\text{A}$	$I_B = 0.2\text{A}$			1.5	
$t_{on}$	Turn-On Time	$I_C = 1\text{A}$	$I_B = 0.1\text{A}$			500	ns
$t_{off}$	Turn-Off Time	$I_C = 1\text{A}$	$I_B = 0.1\text{A}$			2.5	$\mu\text{s}$